

10022T-6152200T

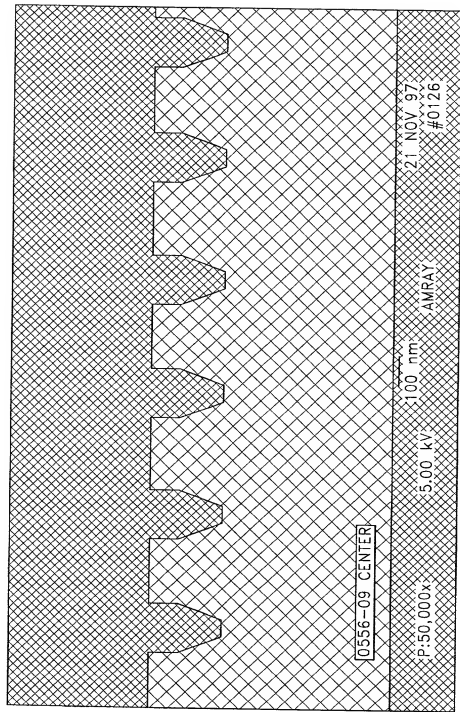


FIG. 1
(PRIOR ART)

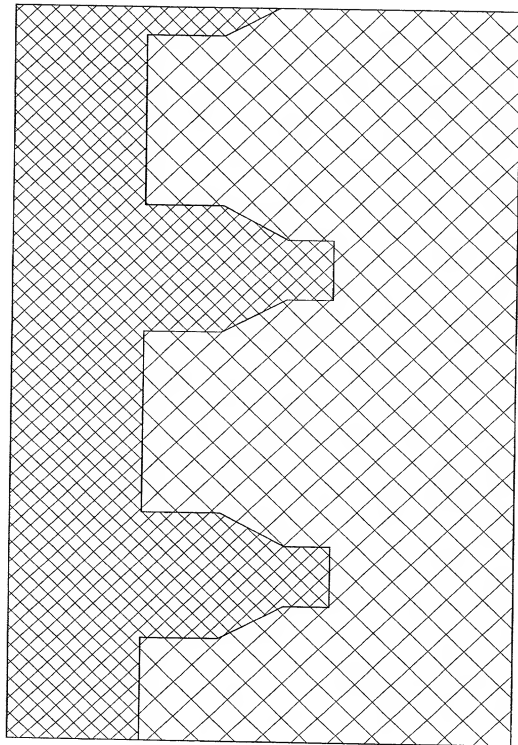


FIG. 2
(PRIOR ART)

process: Flowfill + H_2SO_4 dip + 1000°C anneal

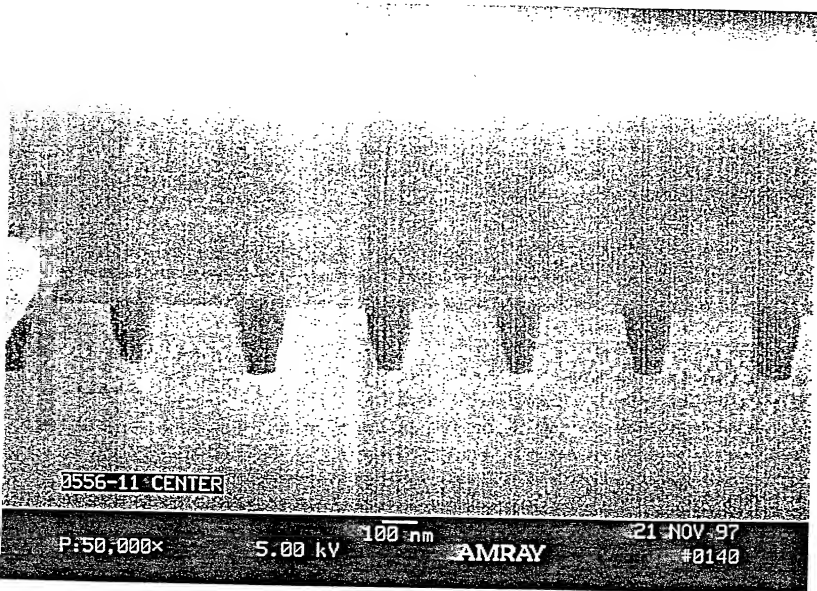


FIG. 3

process: Flowfill + H_2SO_4 dip + 1000°C anneal

enlarged picture of wafer #11

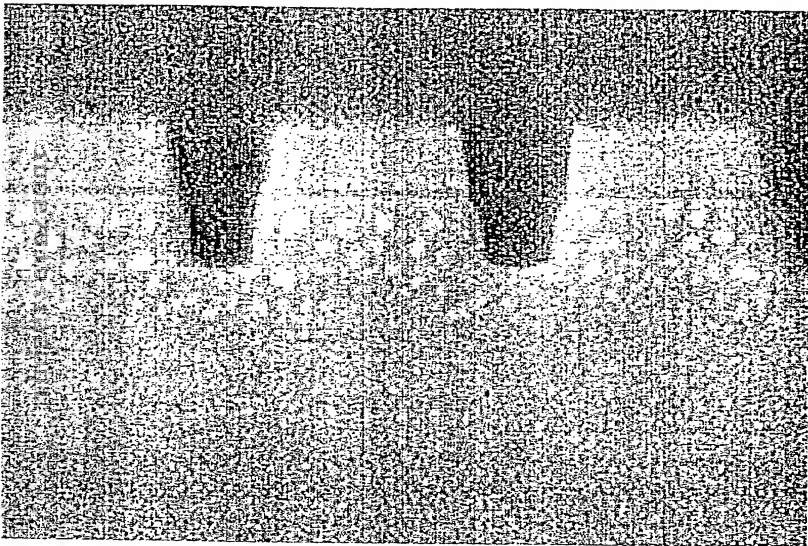


FIG. 4

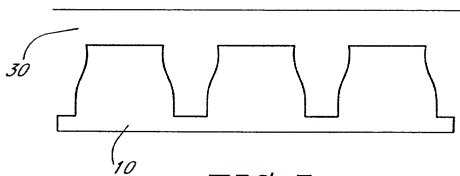


FIG. 5

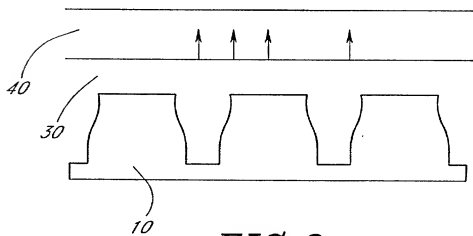


FIG. 6

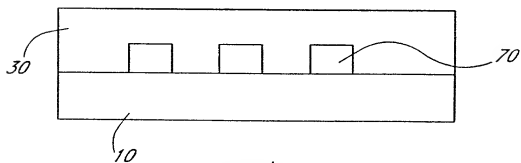


FIG. 7

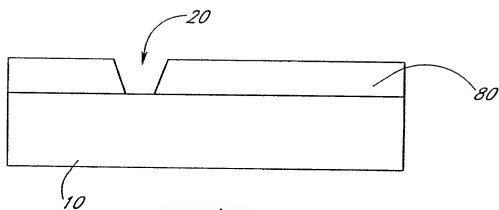


FIG. 8